



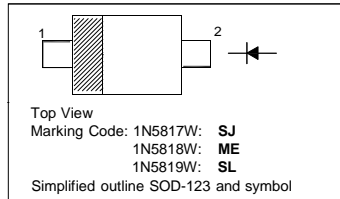
**THE DATASHEET OF  
1N5819W**



## 1A Surface Mount Schottky Barrier Diode

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

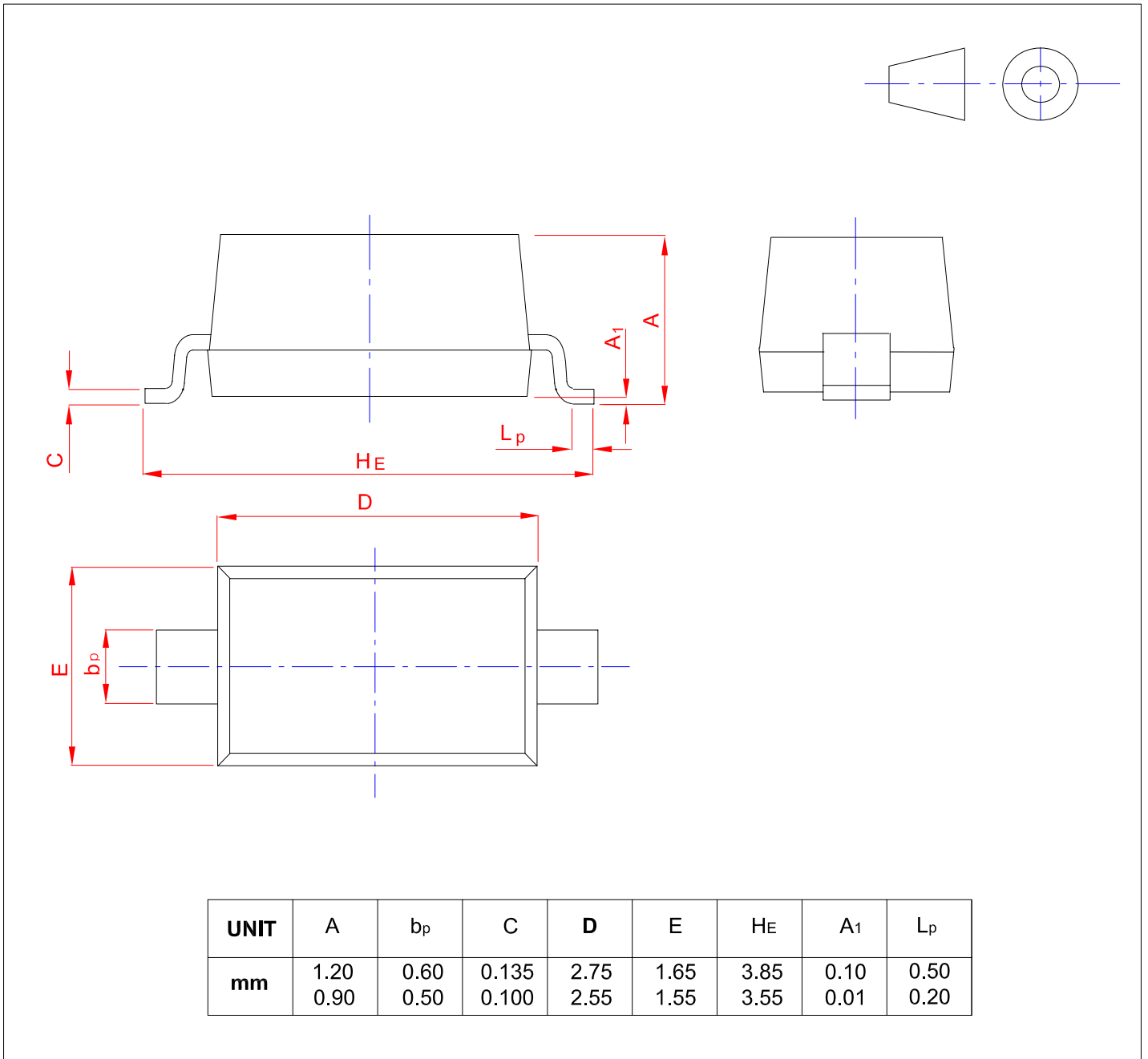
Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	1N5817W: 20 1N5818W: 30 1N5819W: 40	V
Average Forward Rectified Current		$I_{F(AV)}$	1 A
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine-Wave)		$I_{FSM}$	9 A
Power Dissipation	$P_{tot}$	450	mW
Operating Temperature Range	$T_j$	- 55 to + 125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit		
Reverse Breakdown Voltage at $I_R = 1\text{ mA}$	$V_{(BR)R}$	1N5817W: 20 1N5818W: 30 1N5819W: 40	-	V		
Reverse Current at $V_R = 20\text{ V}$		$I_R$	1N5817W: - 1N5818W: - 1N5819W: -	1	mA	
at $V_R = 30\text{ V}$			-	1		
at $V_R = 40\text{ V}$	-		1			
at $V_R = 4\text{ V}$	-		0.05			
at $V_R = 6\text{ V}$	-		0.075			
Forward Voltage at $I_F = 0.1\text{ A}$	$V_F$	1N5819W: -	0.45	V		
at $I_F = 1\text{ A}$		1N5817W: - 1N5818W: - 1N5819W: -	0.45 0.55 0.6			
at $I_F = 3\text{ A}$		1N5817W: - 1N5818W: - 1N5819W: -	0.75 0.875 0.9			
Total Capacitance at $V_R = 4\text{ V}$ , $f = 1\text{ MHz}$		$C_{tot}$	-		120	pF

Plastic surface mounted package; 2 leads

SOD-123



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